**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

# 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-4.2	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -10 V; $I_D$ = -4.2 A; $T_j$ = 25 °C		-	35	45	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S S 017aaa259

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV50EPEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV50EPEA	DQ%

[1] % = placeholder for manufacturing site code

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
$V_{GS}$	gate-source voltage	_		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C	[1]	-	-4.2	Α
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	[1]	-	-2.7	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	-16.9	Α
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = -1.3 A; DUT in avalanche (unclamped)		-	19.5	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	480	mW
			[1]	-	1.2	W
		T <sub>sp</sub> = 25 °C		-	6.95	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-4	Α
ESD maxim	num rating		'	'	'	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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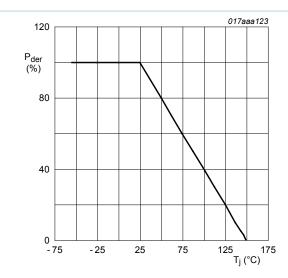


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

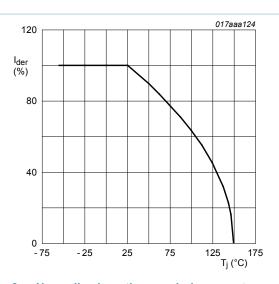


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

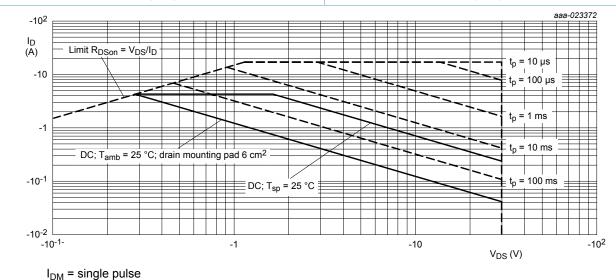


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

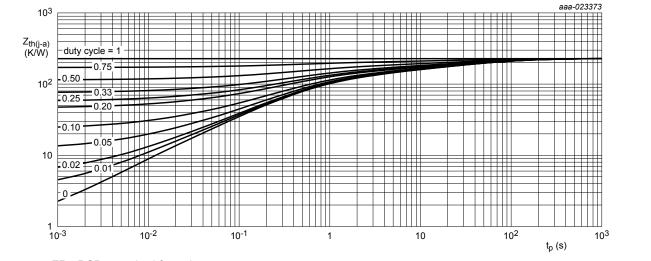
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	227	261	K/W
	from junction to ambient		[2]	-	91	104	K/W

PMV50EPEA

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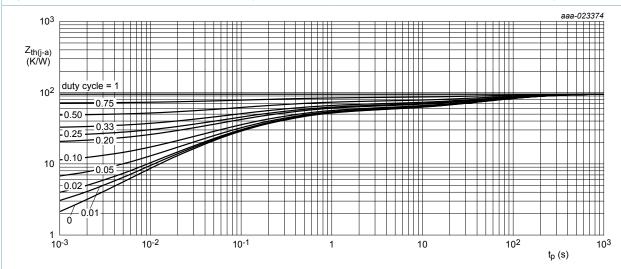
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 10. Characteristics

Table 7 Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
racteristics					
drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-30	-	-	V
gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1	-2	-3	V
drain leakage current	V <sub>DS</sub> = -30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
drain-source on-state	$V_{GS}$ = -10 V; $I_D$ = -4.2 A; $T_j$ = 25 °C	-	35	45	mΩ
resistance	V <sub>GS</sub> = -10 V; I <sub>D</sub> = -4.2 A; T <sub>j</sub> = 150 °C	-	51	67	mΩ
	$V_{GS}$ = -4.5 V; $I_D$ = -3.3 A; $T_j$ = 25 °C	-	49	72	mΩ
forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -4.2 A; $T_j$ = 25 °C	-	13.5	-	S
gate resistance	f = 1 MHz	-	13	-	Ω
characteristics					
total gate charge	$V_{DS}$ = -15 V; $I_{D}$ = -4.2 A; $V_{GS}$ = -10 V;	-	12.8	19.2	nC
gate-source charge	T <sub>j</sub> = 25 °C	-	2.2	-	nC
gate-drain charge		-	2.2	-	nC
input capacitance	$V_{DS}$ = -15 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	793	-	pF
output capacitance	T <sub>j</sub> = 25 °C	-	134	-	pF
reverse transfer capacitance		-	84	-	pF
turn-on delay time	$V_{DS}$ = -15 V; $I_{D}$ = -4.2 A; $V_{GS}$ = -10 V;	-	6	-	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	19	-	ns
turn-off delay time		-	36	-	ns
fall time		-	19	-	ns
ain diode	1	1		1	
source-drain voltage	I <sub>S</sub> = -4 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	_	-0.75	-1.2	V
	drain-source breakdown voltage  gate-source threshold voltage  drain leakage current  gate leakage current  drain-source on-state resistance  forward transconductance gate resistance  total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time  ain diode	racteristics  drain-source breakdown voltage  gate-source threshold voltage  drain leakage current $V_{DS} = -30 \text{ V}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ gate leakage current $V_{DS} = -30 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; 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\ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -30           gate-source threshold voltage $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ -1           drain leakage current gate leakage current $V_{DS} = -30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -10 \ V; \ V_{DS} = -3.3 \ A; \ T_j = 25 \ ^{\circ}C$ -           forward transconductance $V_{DS} = -10 \ V; \ V_{DS} = -4.2 \ A; \ T_j = 25 \ ^{\circ}C$ -           gate resistance $f = 1 \ MHz$ -           sharacteristics         total gate charge $V_{DS} = -15 \ V; \ I_{D} = -4.2 \ A; \ V_{GS} = -10 \ V;$ -           gate-source charge $V_{DS} = -15 \ V; \ I_{D} = -4.2 \ A; \ V_{GS} = 0 \ V;$ -           input capacitance $V_{DS} = -15 \ $	tracteristics           drain-source breakdown voltage $I_D = -250  \mu \text{A};  V_{GS} = 0  V;  T_j = 25  ^{\circ} \text{C}$ -30         -           gate-source threshold voltage $I_D = -250  \mu \text{A};  V_{DS} = V_{GS};  T_j = 25  ^{\circ} \text{C}$ -1         -2           drain leakage current voltage $V_{DS} = -30  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ} \text{C}$ -         -           gate leakage current voltage $V_{GS} = 20  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ} \text{C}$ -         - $V_{GS} = 10  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ} \text{C}$ -         -         - $V_{GS} = 10  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ} \text{C}$ -         -           drain-source on-state resistance $V_{GS} = -10  V;  I_D = -4.2  A;  T_j = 25  ^{\circ} \text{C}$ -         -           drain-source on-state resistance $V_{GS} = -10  V;  I_D = -4.2  A;  T_j = 25  ^{\circ} \text{C}$ -         -           drain-source on-state resistance $V_{GS} = -10  V;  I_D = -4.2  A;  T_j = 25  ^{\circ} \text{C}$ -         -           drain-source on-state resistance $V_{DS} = -10  V;  I_D = -4.2  A;  T_j = 25  ^{\circ} \text{C}$ -         -           fonward transconductance $V_{DS} = -15  V;  I_D = -4.2  A;  V_{GS} = -10  V;$ -         13.5           shara	tracteristics           drain-source breakdown voltage $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -30         -         -           gate-source threshold voltage $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ -1         -2         -3           drain leakage current $V_{DS} = -30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -         -         -1           gate leakage current $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -         -         -10 $V_{GS} = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -         -         -10 $V_{GS} = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -         -         -10 $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -         -         -         -           drain-source on-state resistance $V_{GS} = -10 \ V; \ I_D = -4.2 \ A; \ T_j = 25 \ ^{\circ}C$ -         -

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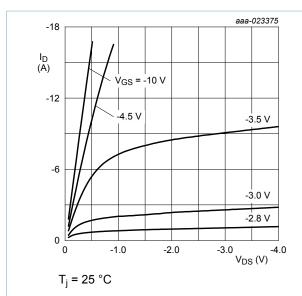


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

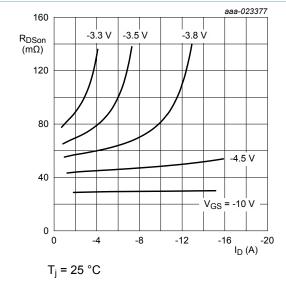


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

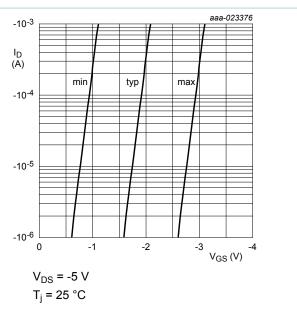


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

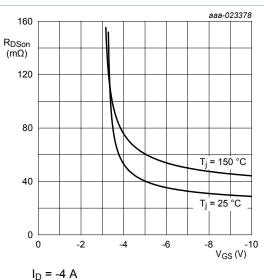


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

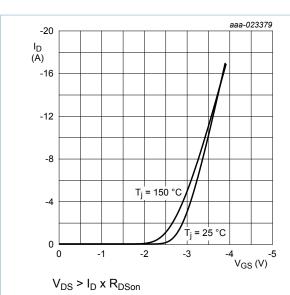


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

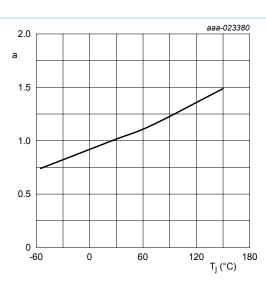


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

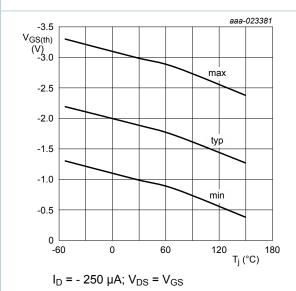


Fig. 12. Gate-source threshold voltage as a function of junction temperature

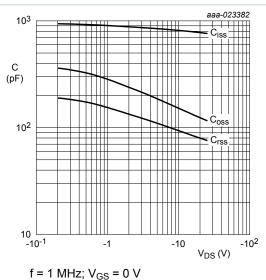


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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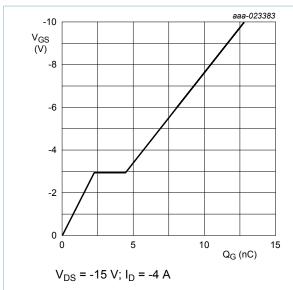


Fig. 15. Gate charge waveform definitions

Q<sub>GS1</sub>

Q<sub>GS2</sub>

Q<sub>G(tot)</sub>-

003aaa508

Q<sub>GS</sub>

V<sub>DS</sub> \_\_\_\_

 $V_{\text{GS}(\text{pl})}$ 

 $\begin{array}{c} V_{GS(th)} \\ V_{GS} \end{array}$ 

Fig. 14. Gate-source voltage as a function of gate charge; typical values

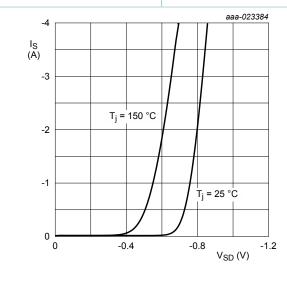
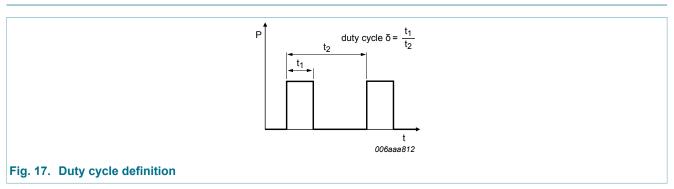


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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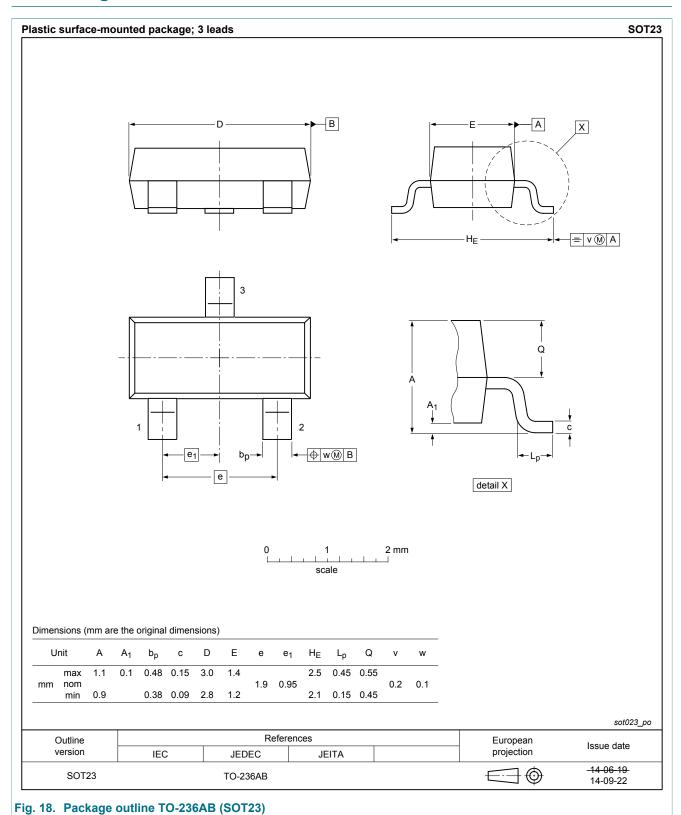
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# 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

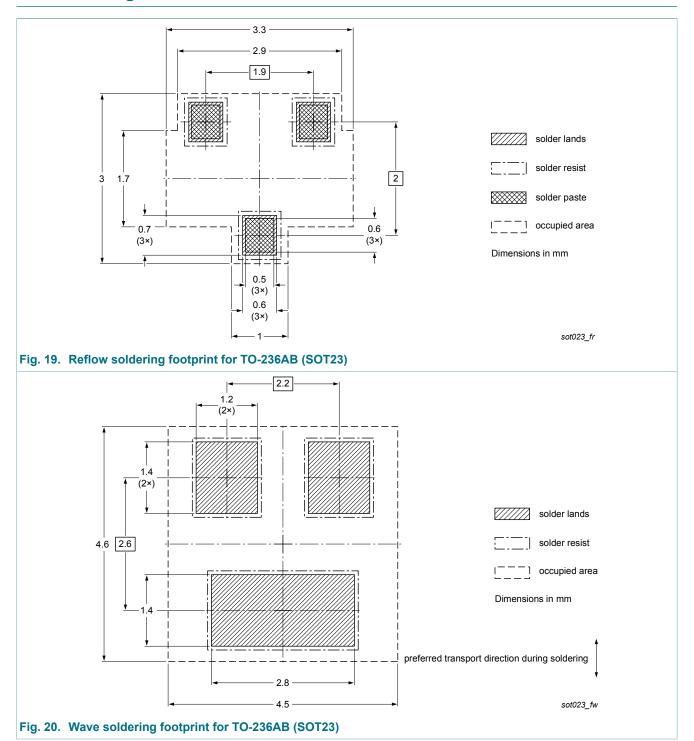
# 12. Package outline



PMV50EPEA

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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV50EPEA v.1	20160630	Product data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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